DATA SHEET



MOS INTEGRATED CIRCUIT μ PD23C128040L

128M-BIT MASK-PROGRAMMABLE ROM 16M-WORD BY 8-BIT (BYTE MODE) / 8M-WORD BY 16-BIT (WORD MODE) PAGE ACCESS MODE

Description

The μ PD23C128040L is a 134,217,728 bits mask-programmable ROM. The word organization is selectable (BYTE mode : 16,777,216 words by 8 bits, WORD mode : 8,388,608 words by 16 bits).

The active levels of OE (Output Enable Input) can be selected with mask-option.

The μ PD23C128040L is packed in 48-pin plastic TSOP(I).

Features

Word organization

16,777,216 words by 8 bits (BYTE mode) 8,388,608 words by 16 bits (WORD mode)

Page access mode

BYTE mode : 8 byte random page access

WORD mode : 4 word random page access

 \bullet Operating supply voltage : Vcc = 3.3 V \pm 0.3 V

| Operating supply voltage | Access time / Page access time | Power supply current (Active mode) | Standby current (CMOS level input) |
|-------------------------------|--------------------------------|------------------------------------|------------------------------------|
| Vcc ns (MAX.) | | mA (MAX.) | μΑ (MAX.) |
| $3.3~\text{V}\pm0.3~\text{V}$ | 100 / 30 | 70 | 30 |

Ordering Information

| Part Number | Package |
|-------------------------|---|
| μPD23C128040LGY-xxx-MJH | 48-pin Plastic TSOP(I) (12 x 18) (Normal bent) |
| μPD23C128040LGY-xxx-MKH | 48-pin Plastic TSOP(I) (12 x 18) (Reverse bent) |

(xxx : ROM code suffix No.)

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NEC

* Pin Configurations (Marking Side)

/xxx indicates active low signal.

| | [μPD23C128040LG1-XXX-WJH] | | |
|-----------------|---------------------------|-------------|-------------|
| | F | | |
| WORD, /BYTE O | 1 48 | <u> </u> | GND |
| A16 O | 2 47 | 0 | GND |
| A15 🔾 🗕 | 3 46 | 0 | O15, A–1 |
| A14 O | 4 45 | O | 07 |
| A13 🔾 🗕 | 5 44 | -0 | O14 |
| A12 〇 | 6 43 | ~ 0 | O6 |
| A11 〇——► | 7 42 | 0 | O13 |
| A10 〇 | 8 41 | 0 | O5 |
| A9 () | 9 40 | O | O12 |
| A8 () | 10 39 | O | O4 |
| A19 🔾 🛏 | 11 38 | 0 | Vcc |
| A21 () | 12 37 | 0 | Vcc |
| A20 🔾 🗕 | 13 36 | 0 | A22 |
| A18 〇——► | 14 35 | 0 | O11 |
| A17 ⊖ ► | 15 34 | 0 | O3 |
| A7 () | 16 33 | 0 | O10 |
| A6 O | 17 32 | 0 | O2 |
| A5 O | 18 31 | O | O9 |
| A4 O | 19 30 | ~~ O | 01 |
| A3 () | 20 29 | 0 | O8 |
| A2 ◯ | 21 28 | ~~ O | O0 |
| A1 O | 22 27 | 0 | /OE, OE, DC |
| A0 O | 23 26 | 0 | GND |
| /CE O | 24 25 | | GND |
| | | 1 | |

48-pin plastic TSOP(I) (12 x 18) (Normal bent)

[µPD23C128040LGY-xxx-MJH]

| A0 - A22 | : Address inputs |
|-------------------|-------------------------------|
| 00 - 07, 08 - 014 | : Data outputs |
| O15, A–1 | : Data output 15 (WORD mode), |
| | LSB Address input (BYTE mode) |
| WORD, /BYTE | : Mode select |
| /CE | : Chip Enable |
| /OE, OE | : Output Enable |
| Vcc | : Supply voltage |
| GND | : Ground |
| DC | : Don't Care |

Remark Refer to Package Drawings for the 1-pin index mark.

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| | 48 1 | | WORD, /BYTE |
|----------------------|-------|---|-------------|
| | 47 2 | | A16 |
| 015, A–1 | 46 3 | | A15 |
| 07 🖂 | 45 4 | | A14 |
| 014 _ | 44 5 | | A13 |
| O6 🔾 🗕 | 43 6 | | A12 |
| 013 _ | 42 7 | | A11 |
| O5 🕞 🗕 | 41 8 | | A10 |
| 012 () - | 40 9 | 0 | A9 |
| 04 🕞 | 39 10 | | A8 |
| Vcc () | 38 11 | | A19 |
| Vcc O | 37 12 | | A21 |
| A22 🔿 🗕 🕨 | 36 13 | | A20 |
| 011 O - | 35 14 | | A18 |
| O3 🔾 🗕 | 34 15 | | A17 |
| O10 ⊖ - | 33 16 | | A7 |
| 02 🖂 | 32 17 | | A6 |
| O9 🔾 🗕 | 31 18 | | A5 |
| 01 🖂 | 30 19 | | A4 |
| O8 🔾 🗕 | 29 20 | | A3 |
| O0)- | 28 21 | | A2 |
| /OE, OE, DC ○ | 27 22 | | A1 |
| | 26 23 | | A0 |
| GND O | 25 24 | | /CE |
| | | 1 | |

48-pin plastic TSOP(I) (12 x 18) (Reverse bent)

[µPD23C128040LGY-xxx-MKH]

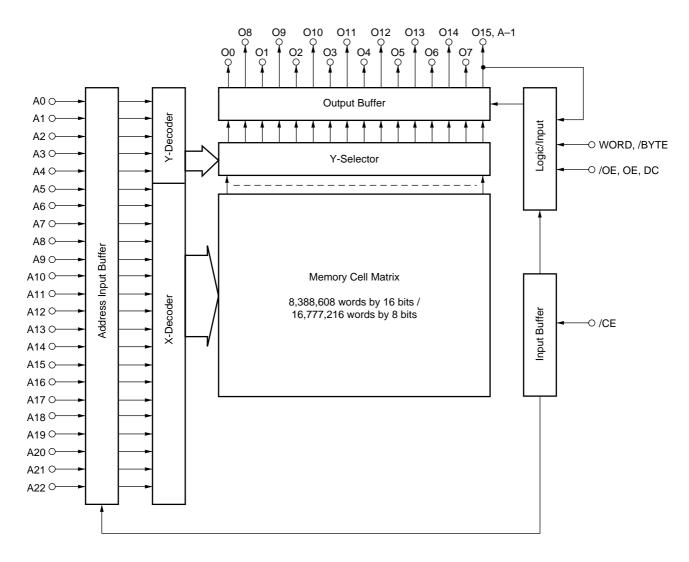
| A0 - A22 | : Address inputs |
|-------------------|-------------------------------|
| 00 - 07, 08 - 014 | : Data outputs |
| O15, A–1 | : Data output 15 (WORD mode), |
| | LSB Address input (BYTE mode) |
| WORD, /BYTE | : Mode select |
| /CE | : Chip Enable |
| /OE, OE | : Output Enable |
| Vcc | : Supply voltage |
| GND | : Ground |
| DC | : Don't Care |
| | |

Remark Refer to **Package Drawings** for the 1-pin index mark.

Input / Output Pin Functions

| Pin name | Input / Output | Function | | |
|-----------------------------|----------------|---|--|--|
| WORD, /BYTE | Input | The pin for switching WORD mode and BYTE mode. | | |
| | | High level : WORD mode (8M-word by 16-bit) | | |
| | | Low level : BYTE mode (16M-word by 8-bit) | | |
| A0 to A22 | Input | Address input pins. | | |
| (Address inputs) | | A0 to A22 are used differently in the WORD mode and the BYTE mode. | | |
| | | WORD mode (8M-word by 16-bit) | | |
| | | A0 to A22 are used as 23 bits address signals. | | |
| | | BYTE mode (16M-word by 8-bit) | | |
| | | A0 to A22 are used as the upper 23 bits of total 24 bits of address signal. | | |
| | | (The least significant bit (A–1) is combined to O15.) | | |
| O0 to O7, O8 to O14 | Output | Data output pins. | | |
| (Data outputs) | | O0 to O7, O8 to O14 are used differently in the WORD mode and the BYTE mode. | | |
| | | WORD mode (8M-word by 16-bit) | | |
| | | The lower 15 bits of 16 bits data outputs to O0 to O14. | | |
| | | (The most significant bit (O15) combined to A–1.) | | |
| | | BYTE mode (16M-word by 8-bit) | | |
| | | 8 bits data outputs to O0 to O7 and also O8 to O14 are high impedance. | | |
| O15, A–1 | Output, Input | O15, A-1 are used differently in the WORD mode and the BYTE mode. | | |
| (Data output 15, | | WORD mode (8M-word by 16-bit) | | |
| LSB Address input) | | The most significant output data bus (O15). | | |
| | | BYTE mode (16M-word by 8-bit) | | |
| | | The least significant address bus (A-1). | | |
| /CE | Input | Chip activating signal. | | |
| (Chip Enable) | | When the OE is active, output states are following. | | |
| | | High level : High impedance | | |
| | | Low level : Data out | | |
| /OE, OE, DC | Input | Output enable signal. The active level of OE is mask option. The active level of OE | | |
| (Output Enable, Don't Care) | | can be selected from high active, low active and Don't care at order. | | |
| Vcc | _ | Supply voltage | | |
| GND | - | Ground | | |

Block Diagram



Mask Option

The active levels of output enable pin (/OE, OE, DC) are mask programmable and optional, and can be selected from among " 0 " " 1 " " x " shown in the table below.

| Option | /OE, OE, DC | OE active level |
|--------|-------------|-----------------|
| 0 | /OE | L |
| 1 | OE | Н |
| x | DC | Don't care |

Operation modes for each option are shown in the tables below.

Operation mode (Option : 0)

| /CE | /OE | Mode | Output state |
|-----|--------|---------|----------------|
| L | L | Active | Data out |
| | Н | | High impedance |
| н | H or L | Standby | High impedance |

Operation mode (Option : 1)

| /CE | OE | Mode | Output state |
|-----|--------|---------|----------------|
| L | L | Active | High impedance |
| | Н | | Data out |
| н | H or L | Standby | High impedance |

Operation mode (Option : x)

| | /CE | DC | Mode | Output state |
|---|-----|--------|---------|----------------|
| ſ | L | H or L | Active | Data out |
| I | Н | H or L | Standby | High impedance |

Remark L: Low level input

H : High level input

Electrical Specifications

Absolute Maximum Ratings

| Parameter | Symbol | Condition | Rating | Unit |
|-------------------------------|--------|-----------|-----------------|------|
| Supply voltage | Vcc | | -0.3 to +4.6 | V |
| Input voltage | Vı | | –0.3 to Vcc+0.3 | V |
| Output voltage | Vo | | –0.3 to Vcc+0.3 | V |
| Operating ambient temperature | TA | | -10 to +70 | °C |
| Storage temperature | Tstg | | -65 to +150 | °C |

Caution Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Capacitance (TA = 25°C)

| Parameter | Symbol | Test condition | MIN. | TYP. | MAX. | Unit |
|--------------------|--------|----------------|------|------|------|------|
| Input capacitance | С | f = 1 MHz | | | 10 | pF |
| Output capacitance | Co | | | | 12 | pF |

DC Characteristics (T_A = -10 to +70°C, V_{CC} = 3.3 V \pm 0.3 V)

| Parameter | Symbol | Test conditions | MIN. | TYP. | MAX. | Unit |
|---------------------------|--------|------------------------------------|------|------|-----------|------|
| High level input voltage | Vін | | 2.2 | | Vcc + 0.3 | V |
| Low level input voltage | VIL | | -0.3 | | +0.8 | V |
| High level output voltage | Vон | Іон = -100 μА | 2.4 | | | V |
| Low level output voltage | Vol | lo∟ = 2.1 mA | | | 0.4 | V |
| Input leakage current | lu | $V_1 = 0 V$ to V_{CC} | -10 | | +10 | μA |
| Output leakage current | Ilo | Vo = 0 V to Vcc, Chip deselected | -10 | | +10 | μA |
| Power supply current | Icc1 | /CE = VIL (Active mode), Io = 0 mA | | | 70 | mA |
| Standby current | Іссз | /CE = Vcc - 0.2 V (Standby mode) | | | 30 | μA |

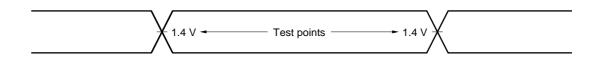
AC Characteristics (T_A = -10 to +70°C, V_{CC} = 3.3 V ± 0.3 V)

| Parameter | Symbol | Test condition | MIN. | TYP. | MAX. | Unit |
|---------------------------|--------------|----------------|------|------|------|------|
| Address access time | tacc | | | | 100 | ns |
| Page access time | t PAC | | | | 30 | ns |
| Chip enable access time | tce | | | | 100 | ns |
| Output enable access time | toe | | | | 30 | ns |
| Output hold time | tон | | 0 | | | ns |
| Output disable time | t DF | | 0 | | 25 | ns |
| WORD, /BYTE access time | twв | | | | 100 | ns |

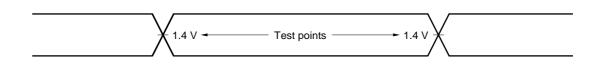
Remark toF is the time from inactivation of /CE or /OE, OE to high-impedance state output.

AC Test Conditions

Input waveform (Rise / Fall time ≤ 5 ns)



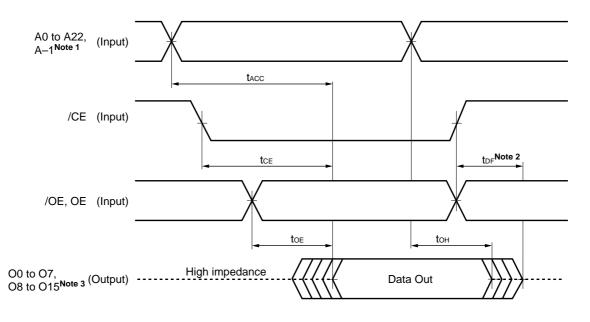
Output waveform



Output load

1TTL + 100 pF

Read Cycle Timing Chart 1

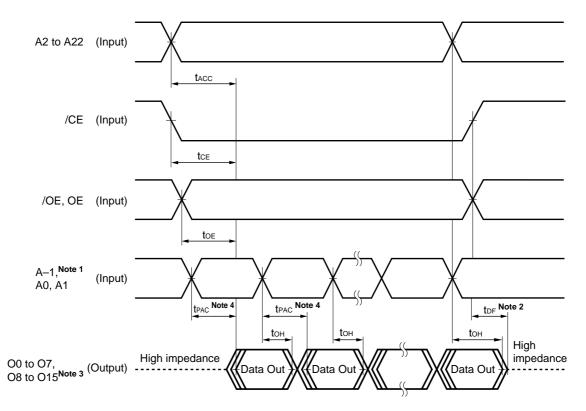


Notes 1. During WORD mode, A-1 is O15.

2. tDF is specified when one of /CE, /OE, OE is inactivated.

3. During BYTE mode, O8 to O14 are high impedance and O15 is A-1.

* Read Cycle Timing Chart 2 (Page Access Mode)

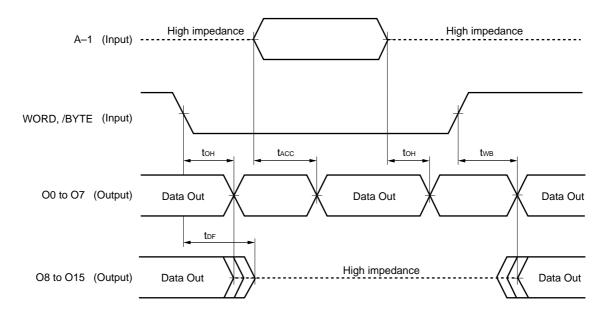


Notes 1. During WORD mode, A–1 is O15.

- **2.** t_{DF} is specified when one of /CE, /OE, OE is inactivated.
- 3. During BYTE mode, O8 to O14 are high impedance and O15 is A-1.
- 4. The definition of page access time is as follows.

| Page access time | Upper address (A2 to A22) | /CE input condition | /OE, OE input condition |
|------------------|---------------------------|---------------------|----------------------------|
| | inputs condition | | |
| t pac | Before tacc – tpac | Before tce - tPAC | Before stabilizing of page |
| | | | address (A-1, A0, A1) |

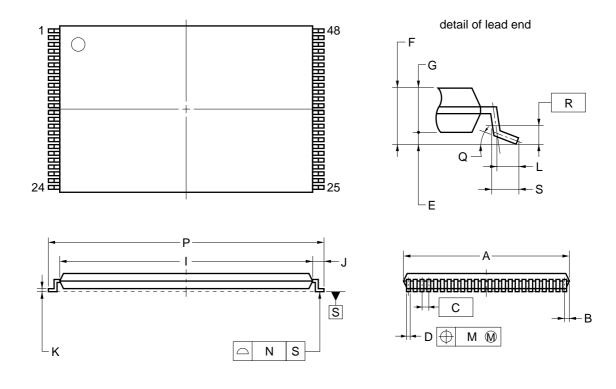
WORD, /BYTE Switch Timing Chart



Remark /OE, OE and /CE : Active.

* Package Drawings

48-PIN PLASTIC TSOP(I) (12x18)



NOTES

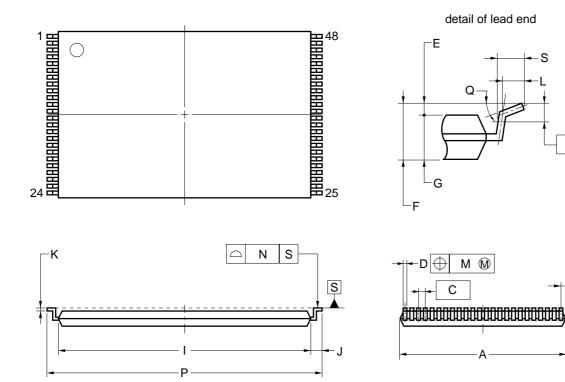
- 1. Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.
- 2. "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX.)

| ITEM | MILLIMETERS |
|------|--------------------------|
| Α | 12.0±0.1 |
| В | 0.45 MAX. |
| С | 0.5 (T.P.) |
| D | 0.22±0.05 |
| Е | 0.1±0.05 |
| F | 1.2 MAX. |
| G | 1.0±0.05 |
| 1 | 16.4±0.1 |
| J | 0.8±0.2 |
| К | 0.145±0.05 |
| L | 0.5 |
| М | 0.10 |
| N | 0.10 |
| Р | 18.0±0.2 |
| Q | 3° ^{+5°} -3° |
| R | 0.25 |
| S | 0.60±0.15 |
| | S48GY-50-MJH1-1 |

R

⊢В

48-PIN PLASTIC TSOP(I) (12x18)



NOTES

- 1. Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.
- 2. "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX.)

| ITEM | MILLIMETERS |
|------|---------------------------------------|
| А | 12.0±0.1 |
| В | 0.45 MAX. |
| С | 0.5 (T.P.) |
| D | 0.22±0.05 |
| E | 0.1±0.05 |
| F | 1.2 MAX. |
| G | 1.0±0.05 |
| I | 16.4±0.1 |
| J | 0.8±0.2 |
| К | 0.145±0.05 |
| L | 0.5 |
| М | 0.10 |
| N | 0.10 |
| Р | 18.0±0.2 |
| Q | $3^{\circ}^{+5^{\circ}}_{-3^{\circ}}$ |
| R | 0.25 |
| S | 0.60±0.15 |
| S | 648GY-50-MKH1-1 |

Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μ PD23C128040L.

Types of Surface Mount Device

| μ PD23C128040LGY-MJH | : 4 | 48-pin plastic TSOP(I) (12 x 18) (Normal bent) |
|--------------------------|-----|---|
| μPD23C128040LGY-MKH | : 4 | 48-pin plastic TSOP(I) (12 x 18) (Reverse bent) |

NOTES FOR CMOS DEVICES -

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

(2) HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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M8E 00.4